

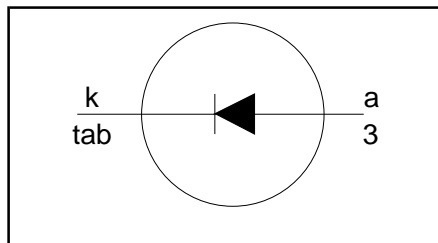
**Rectifier diodes
Schottky barrier**

PBYR745B, PBYR745D series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$V_R = 40\text{ V} / 45\text{ V}$
$I_{F(AV)} = 7.5\text{ A}$
$V_F \leq 0.57\text{ V}$

GENERAL DESCRIPTION

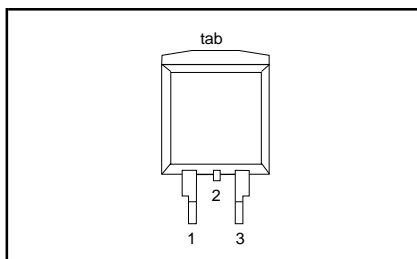
Schottky rectifier diodes in a surface mounting plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR745B series is supplied in the SOT404 surface mounting package.
The PBYR745D series is supplied in the SOT428 surface mounting package.

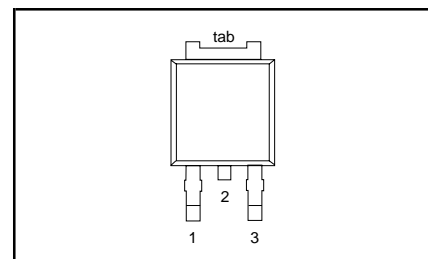
PINNING

PIN	DESCRIPTION
1	no connection
2	cathode ¹
3	anode
tab	cathode

SOT404



SOT428



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
				40B 40D	45B 45D	
V_{RRM}	Peak repetitive reverse voltage	$T_{mb} \leq 114\text{ °C}$	-	40	45	V
V_{RWM}	Working peak reverse voltage		-	40	45	V
V_R	Continuous reverse voltage		-	40	45	V
$I_{F(AV)}$	Average rectified forward current	square wave; $\delta = 0.5$; $T_{mb} \leq 136\text{ °C}$	-	7.5		A
I_{FRM}	Repetitive peak forward current	square wave; $\delta = 0.5$; $T_{mb} \leq 136\text{ °C}$	-	15		A
I_{FSM}	Non-repetitive peak forward current	$t = 10\text{ ms}$ PBYR7..B	-	135		A
		$t = 8.3\text{ ms}$	-	150		A
		$t = 10\text{ ms}$ PBYR7..D	-	100		A
		$t = 8.3\text{ ms}$	-	110		A
I_{RRM}	Peak repetitive reverse surge current	sinusoidal; $T_j = 125\text{ °C}$ prior to surge; with reapplied $V_{RRM(max)}$ pulse width and repetition rate limited by T_{jmax}	-	1		A
T_j	Operating junction temperature		-	150		°C
T_{stg}	Storage temperature		- 65	175		°C

1. It is not possible to make connection to pin 2 of the SOT404 or SOT428 package.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base		-	-	3	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	pcb mounted, minimum footprint, FR4 board	-	50	-	K/W

ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	Forward voltage	$I_F = 7.5\text{ A}; T_j = 125\text{ °C}$ $I_F = 15\text{ A}; T_j = 125\text{ °C}$	-	0.45 0.65	0.57 0.72	V V
I_R	Reverse current	$I_F = 15\text{ A}$ $V_R = V_{RWM}$	-	0.64 0.13	0.84 1	V mA
C_d	Junction capacitance	$V_R = V_{RWM}; T_j = 100\text{ °C}$ $V_R = 5\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ °C to }125\text{ °C}$	-	17 270	22 -	mA pF

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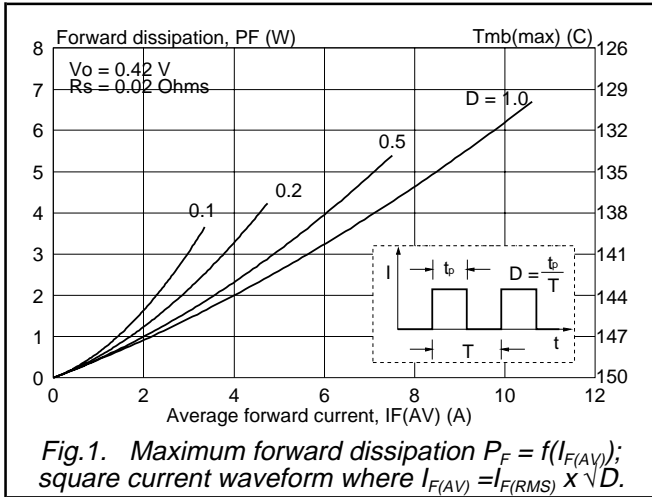


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

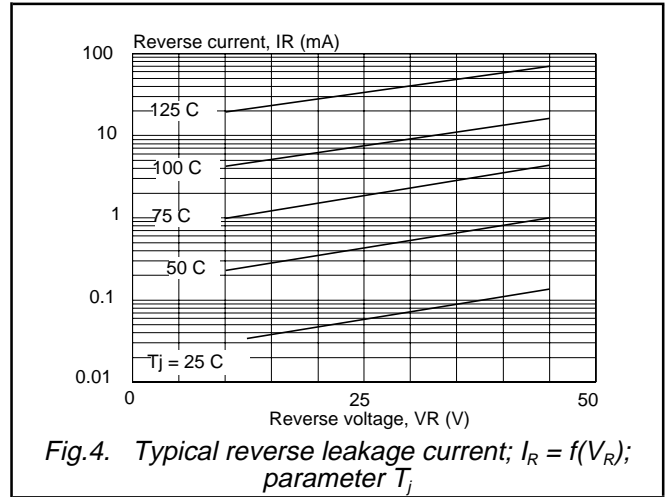


Fig.4. Typical reverse leakage current; $I_R = f(V_R)$; parameter T_j

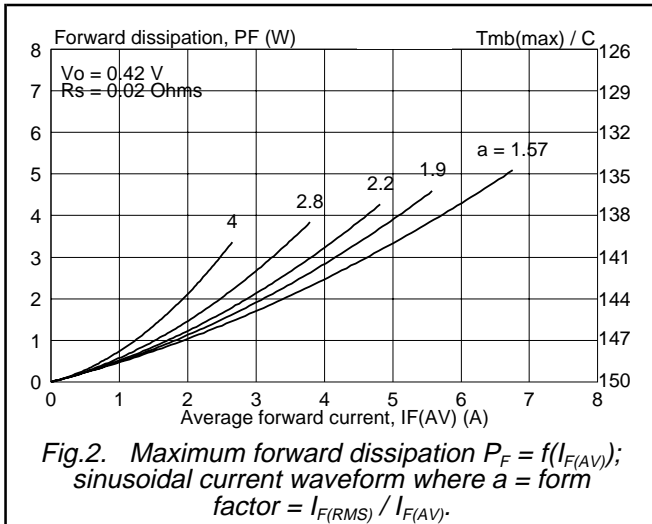


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$; sinusoidal current waveform where $a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$.

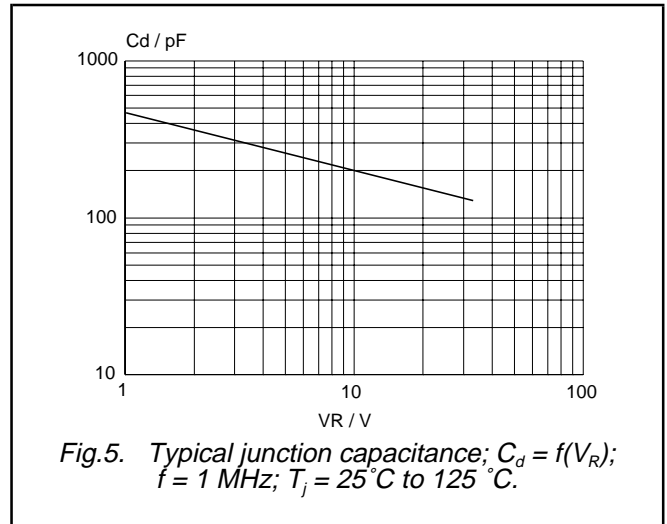


Fig.5. Typical junction capacitance; $C_d = f(V_R)$; $f = 1\text{ MHz}$; $T_j = 25^\circ\text{C}$ to 125°C .

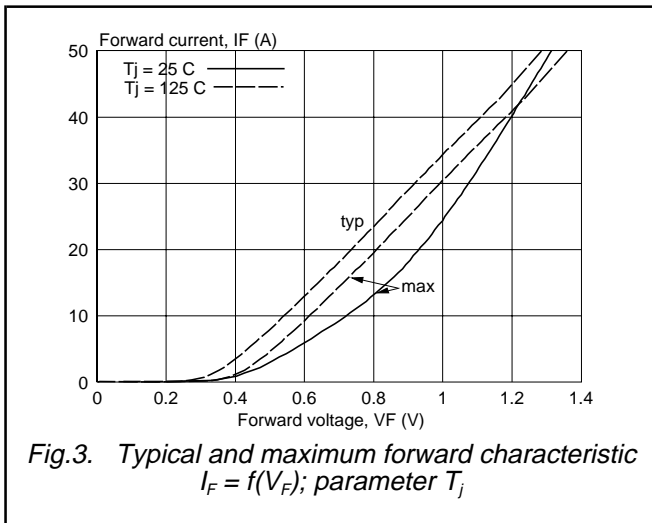


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_j

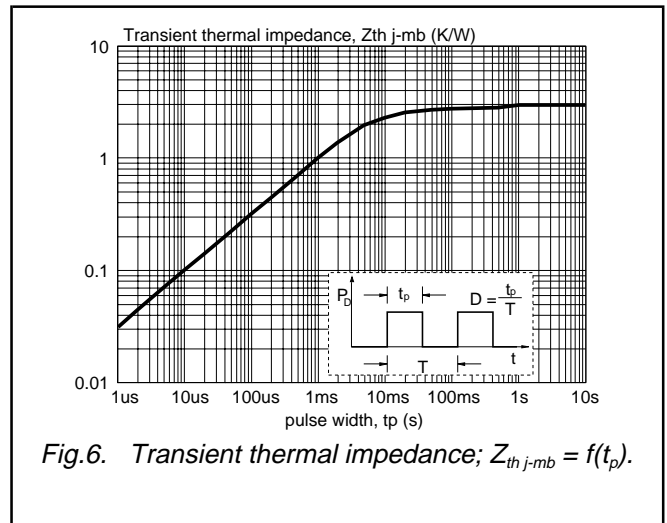
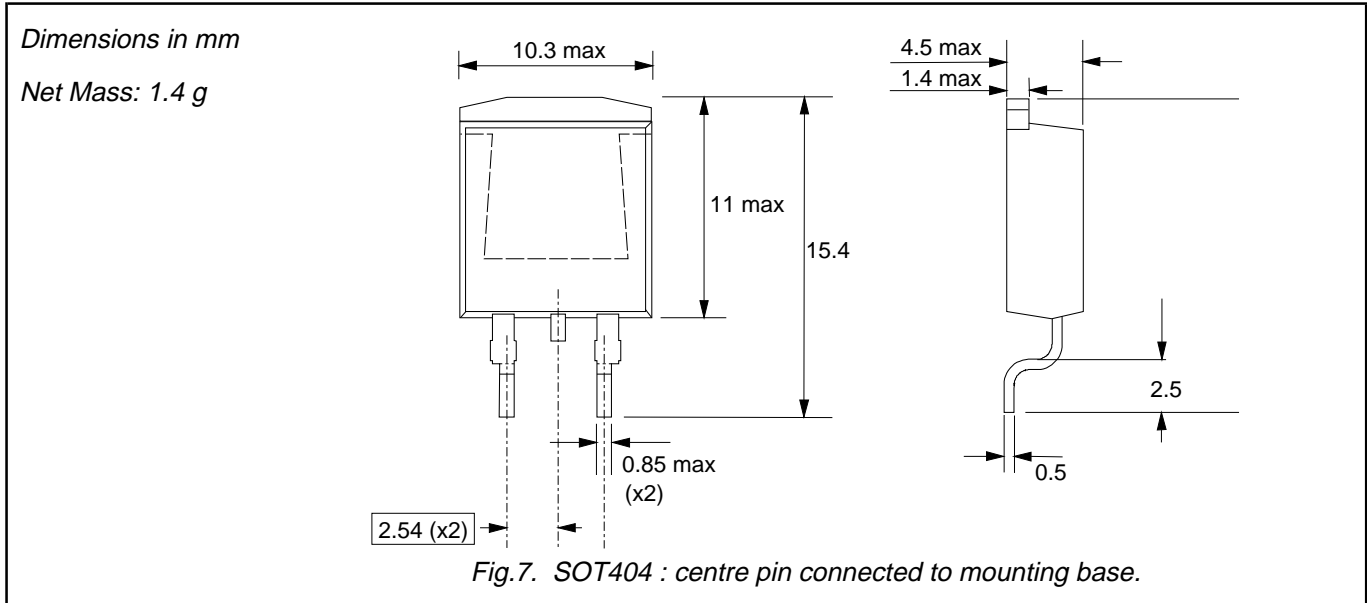


Fig.6. Transient thermal impedance; $Z_{th\ j-mb} = f(t_p)$.

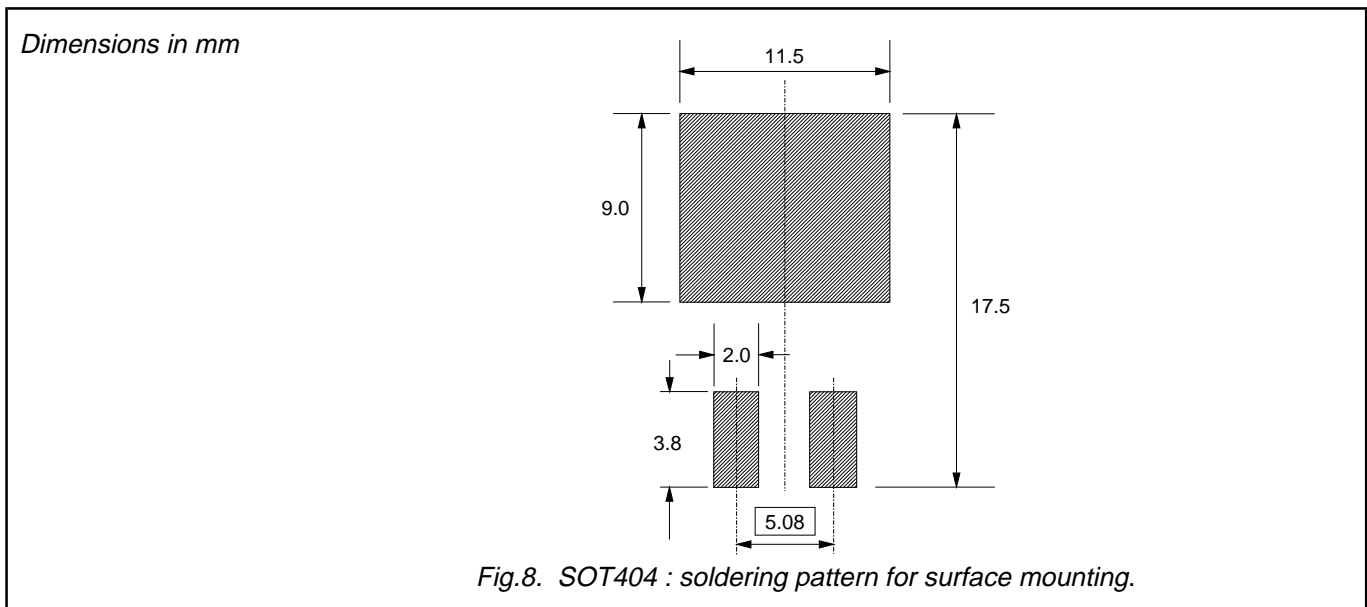
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MECHANICAL DATA



MOUNTING INSTRUCTIONS



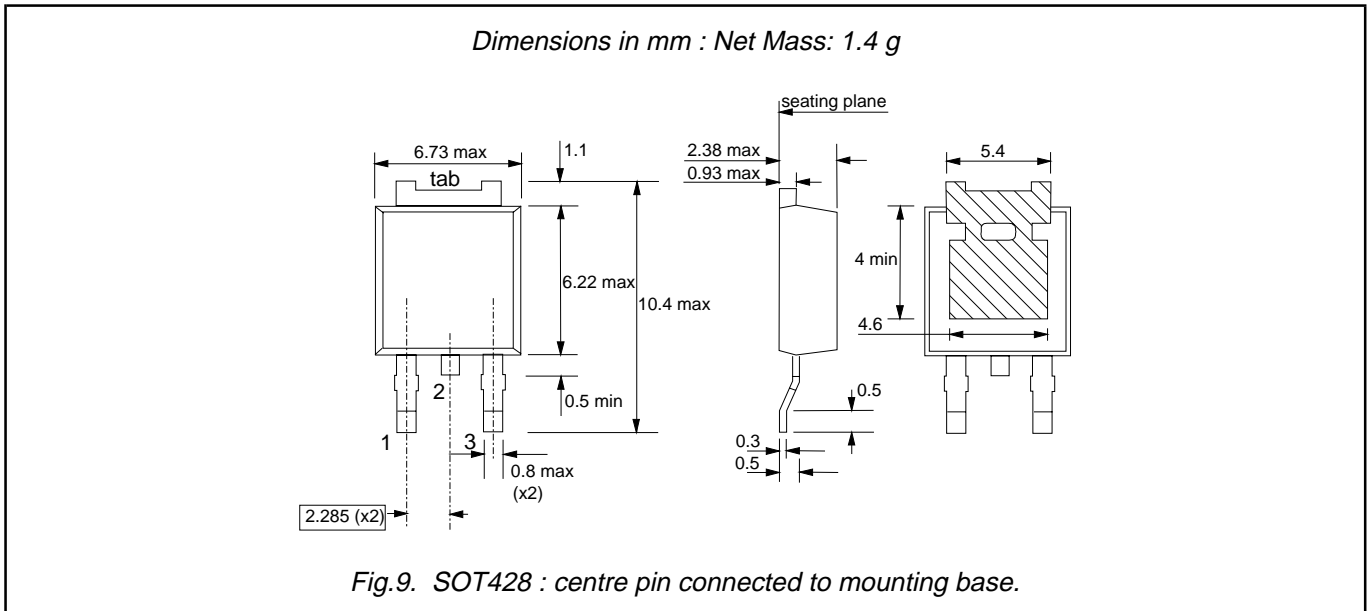
Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Epoxy meets UL94 V0 at 1/8".

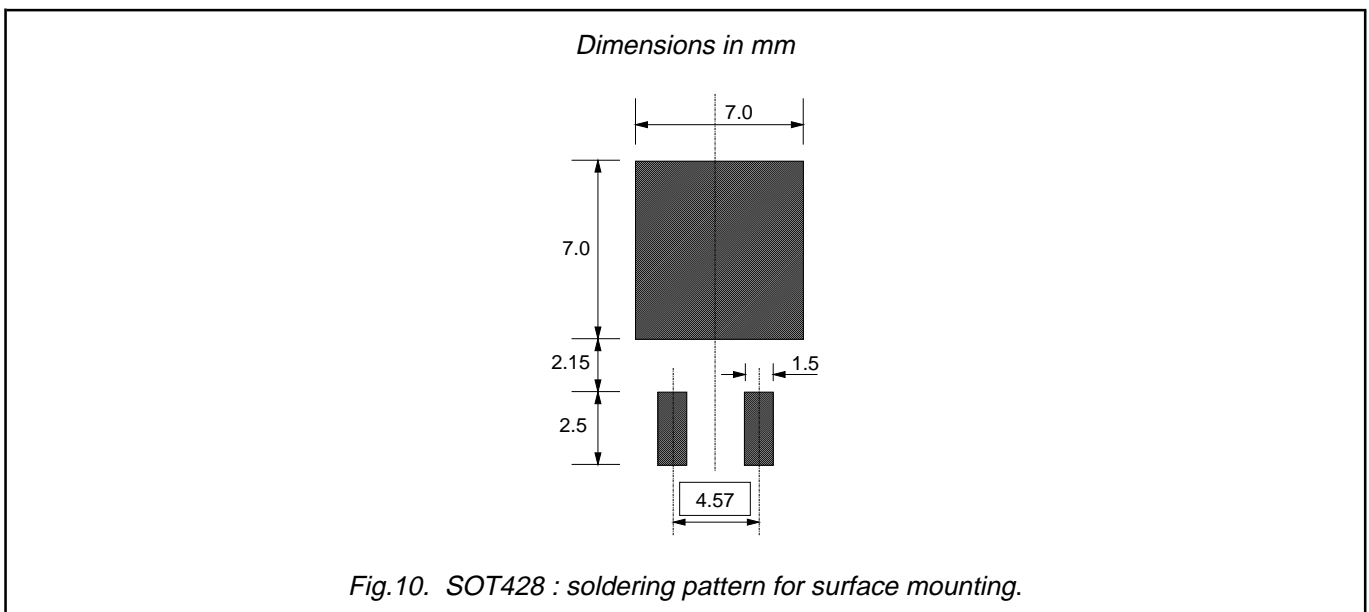
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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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